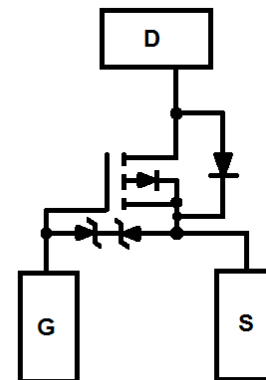
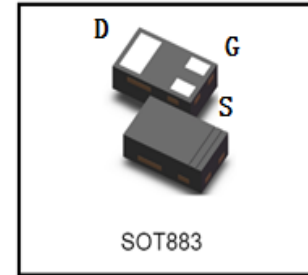


# LP0404N3T5G

20V, P-Channel (D-S) MOSFET

## 1. FEATURES

- $V_{DS} = -20V$   
 $R_{DS(ON)} \leq 0.48\Omega, V_{GS@-4.5V}, I_{DS@-780mA}$   
 $R_{DS(ON)} \leq 0.67\Omega, V_{GS@-2.5V}, I_{DS@-660mA}$   
 $R_{DS(ON)} \leq 0.95\Omega, V_{GS@-1.8V}, I_{DS@-100mA}$   
 $R_{DS(ON)} \leq 2.2\Omega, V_{GS@-1.5V}, I_{DS@-100mA}$
- Super high density cell design for extremely low  $R_{DS(ON)}$ .
- Exceptional on-resistance and maximum DC current capability.
- Gate to Source ESD protection
- MSL:1
- Total shelf life : >10 years
- We declare that the material of product compliance with RoHS requirements and Halogen Free.



## 2. APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System

## 3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LP0404N3T5G	T5	10000/Tape&Reel

## 4. MAXIMUM RATINGS( $T_a = 25^\circ C$ )

Parameter	Symbol	Limits	Unit
Drain-to-Source Voltage	$V_{DSS}$	-20	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 6$	V
Drain Current (Note 1) Steady State	$I_D$	-1.4	A
Power Dissipation	PD	950	mW
Operating and Storage temperature	$T_{op}, T_{stg}$	-55~+150	$^\circ C$

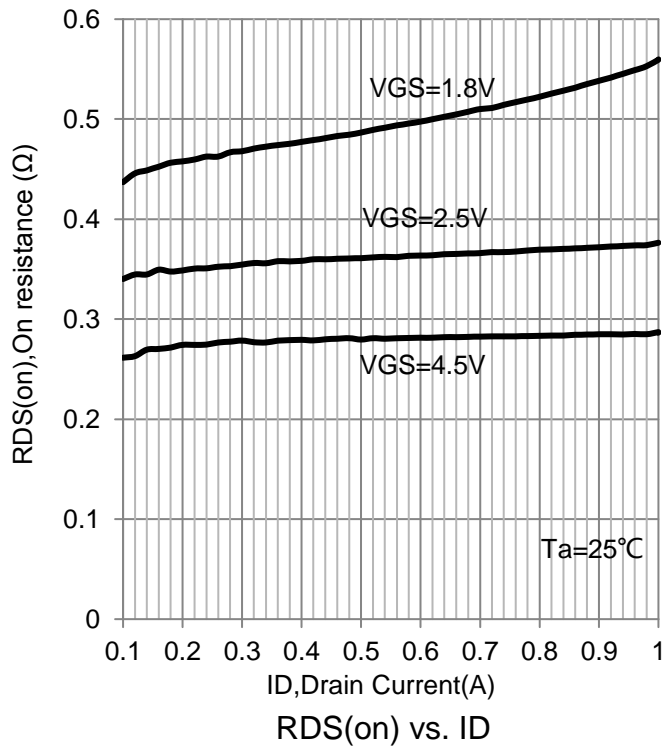
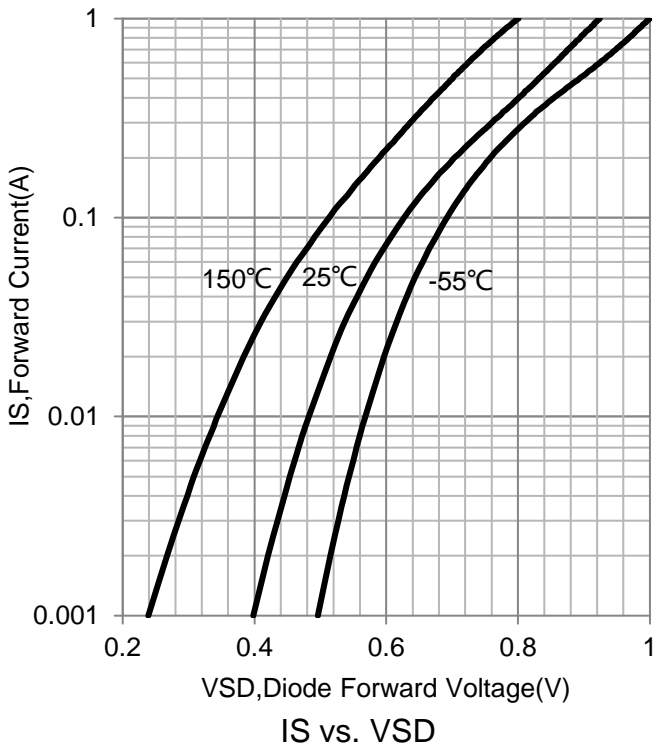
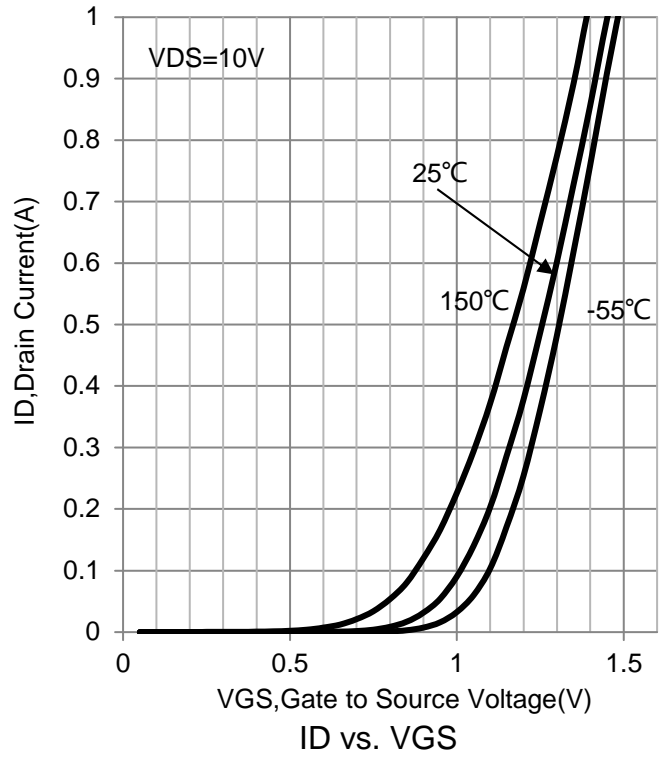
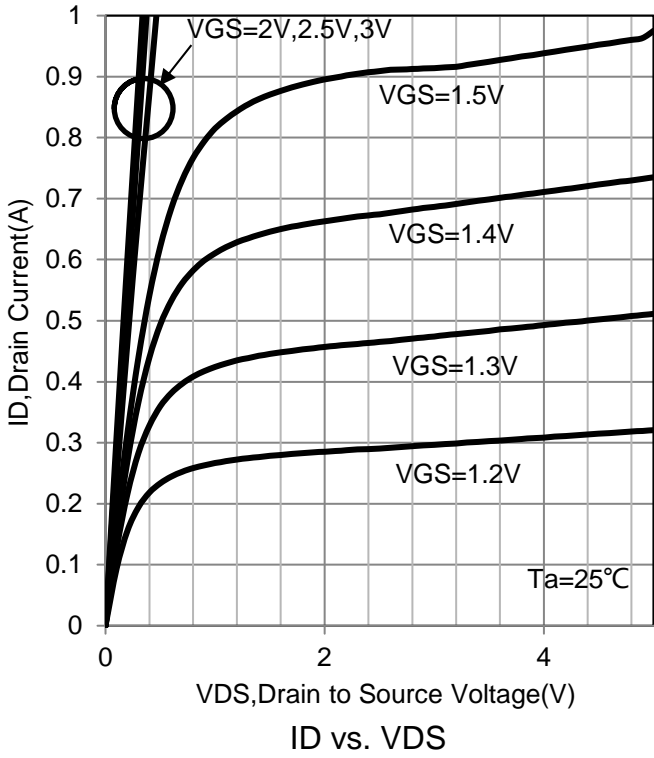
Note 1: Surface Mounted on 1" x 1" FR4 Board.

**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

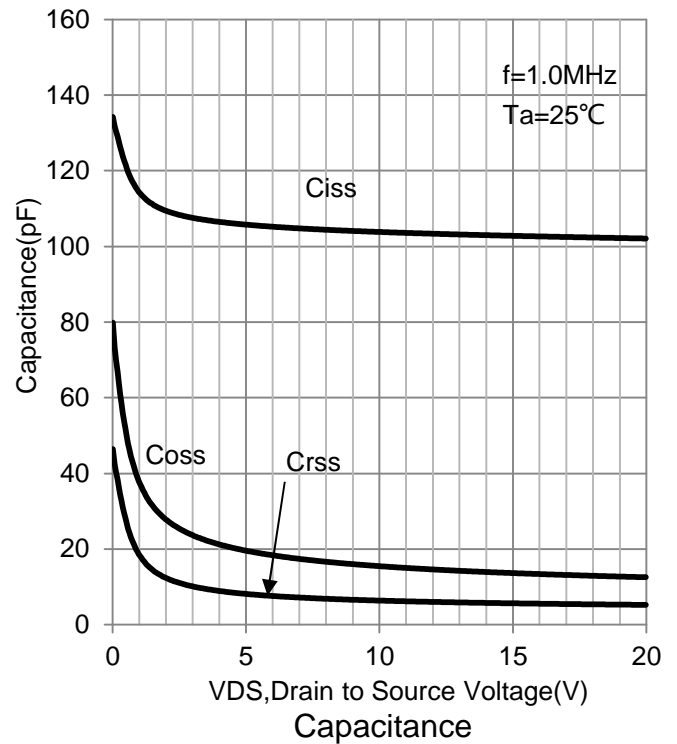
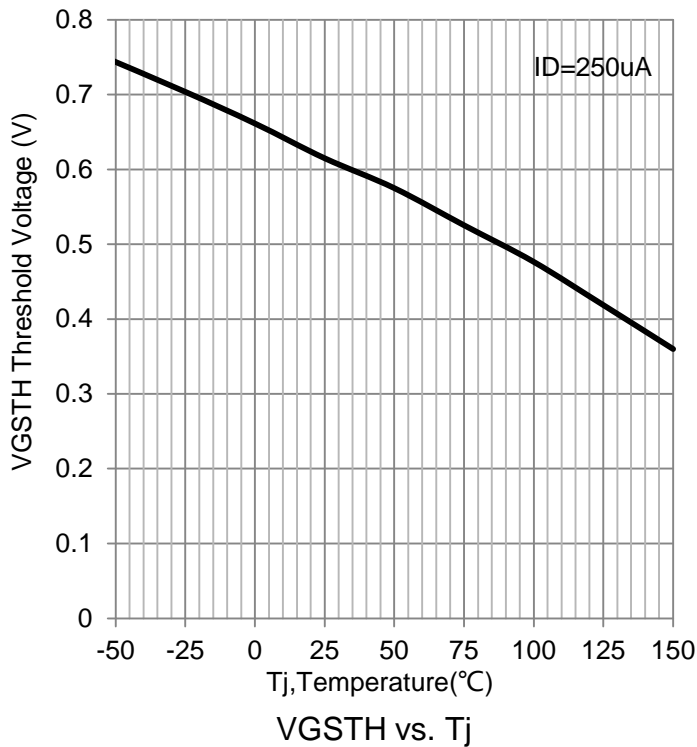
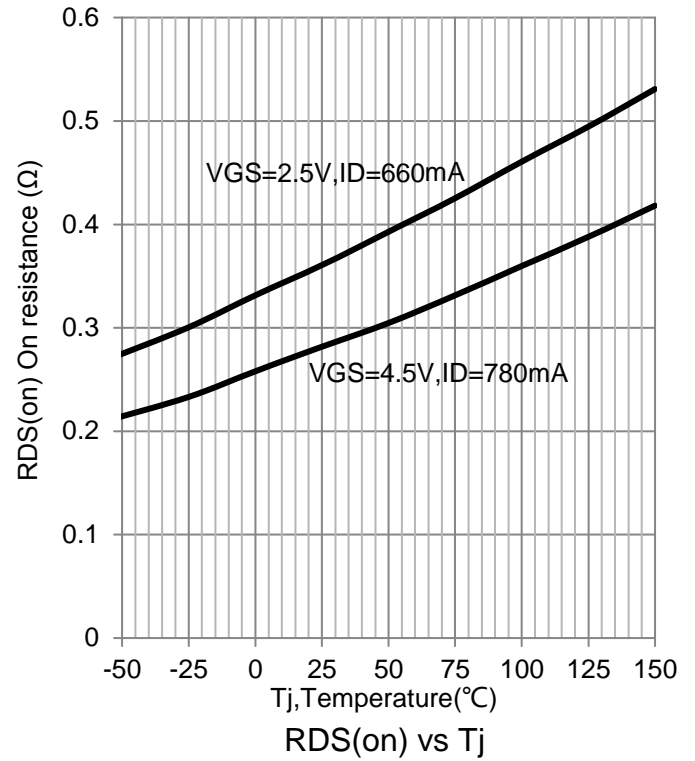
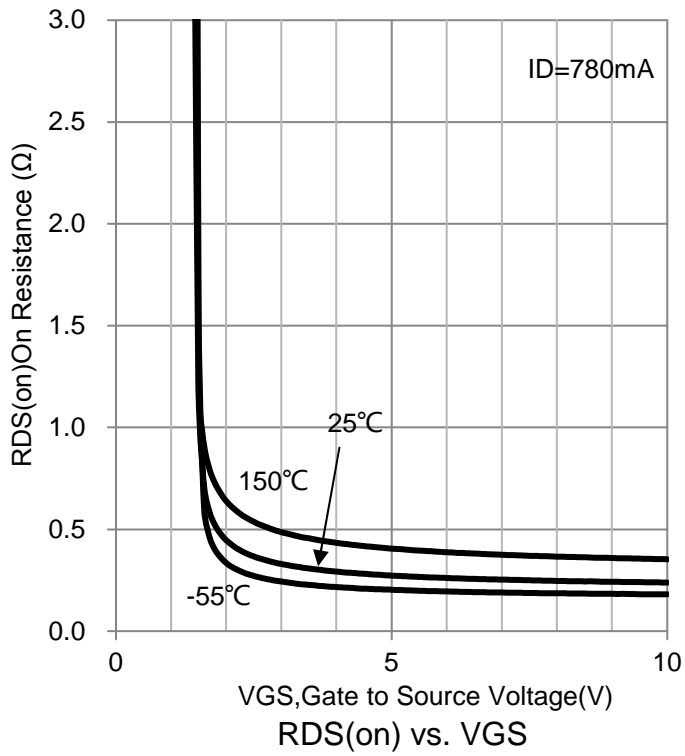
Characteristic	Symbol	Min.	Typ.	Max.	Unit
<b>Static</b>					
Drain-Source Breakdown Voltage (VGS = 0V, ID = -250uA)	V(BR)DSS	-20	-	-	V
Gate Threshold Voltage (VDS =VGS , ID =-250μA)	VGS(th)	-0.4	-0.92	-1.2	V
Gate Leakage Current (VDS =0V, VGS =±4.5V)	IGSS	-	-	±10	μA
Zero Gate Voltage Drain Current (VDS =-16V, VGS =0V)	IDSS	-	-	-1	μA
Drain-Source On-Resistance (VGS=-4.5V,ID=-780mA)	RDS(ON)	-	0.34	0.48	Ω
Drain-Source On-Resistance (VGS=-2.5V,ID=-660mA)		-	0.45	0.67	
Drain-Source On-Resistance (VGS=-1.8V,ID=-100mA)		-	0.72	0.95	
Drain-Source On-Resistance (VGS=-1.5V,ID=-100mA)		-	1.3	2.2	
Diode Forward Voltage (IS =-350mA, VGS =0V)	VSD	-	-0.83	-1.2	V
<b>Dynamic</b>					
Total Gate Charge	(VDS =-16V, VGS =-4.5V, ID =-200mA)	Qg	-	1.14	nC
Gate-Source Charge		Qgs	-	0.3	
Gate-Drain Charge		Qgd	-	0.3	
Turn-On Delay Time	(VDD =-10V, RL =50Ω,VGEN =- 5V,RG =10Ω,ID =-200mA)	td(on)	-	51.3	ns
Rise Time		tr	-	24.2	
Turn-Off Delay Time		td(off)	-	246	
Fall Time		tf	-	81.2	
Input Capacitance	(VDS = -16 V, VGS = 0 V, f = 1 MHz)	Ciss	-	78.2	pF
Output Capacitance		Coss	-	9.68	
Reverse Transfer Capacitance		Crss	-	5.18	

Note 2: Pulse test; pulse width ≤ 300μs, duty cycle ≤ 2%.

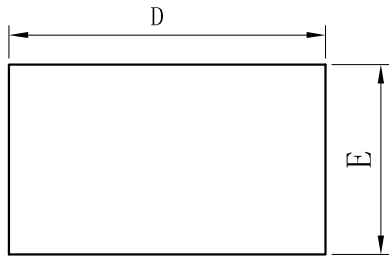
**6. ELECTRICAL CHARACTERISTICS CURVES**



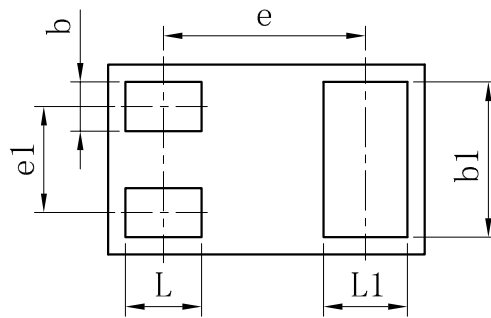
**6. ELECTRICAL CHARACTERISTICS CURVES(Con.)**



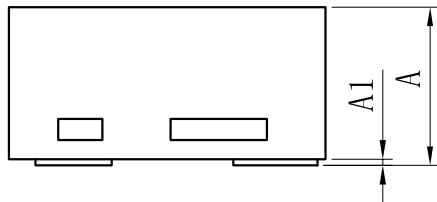
**7.OUTLINE AND DIMENSIONS**



TOP VIEW



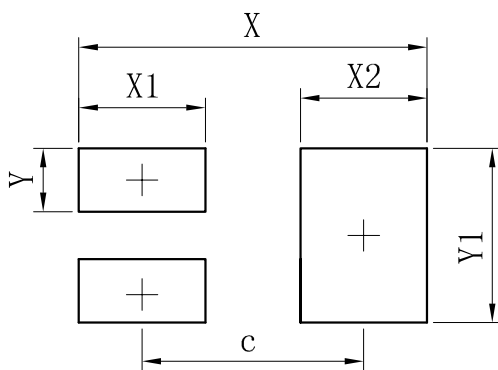
BOTTOM VIEW



SIDE VIEW

SOT883			
Dim	Min	Typ	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	-	0.64	-
e1	-	0.34	-
L	0.19	0.24	0.29
L1	0.22	0.27	0.32
b	0.10	0.15	0.20
b1	0.44	0.49	0.54
A	0.43	0.48	0.53
A1	0	-	0.05
All Dimensions in mm			

**8.SOLDERING FOOTPRINT**



Dimensions	(mm)
c	0.70
X	1.10
X1	0.40
X2	0.40
Y	0.20
Y1	0.55

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)